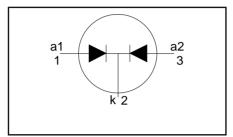
Rectifier diodes ultrafast, rugged

BYQ40EW series

FEATURES

- Low forward volt drop
- Fast switching
- Soft recovery characteristic
- Reverse surge capability
- High thermal cycling performance
- Low thermal resistance

SYMBOL



QUICK REFERENCE DATA

$V_R = 150 \text{ V}/200 \text{ V}$
$V_F \le 0.85 \text{ V}$
$I_{O(AV)} = 40 A$
$I_{RRM} \le 0.2 A$
$t_{rr} \leq 30 \text{ ns}$

GENERAL DESCRIPTION

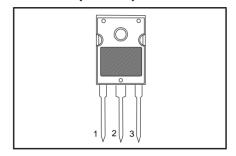
Dual, common cathode, ultra-fast, epitaxial rectifier diodes intended for use as output rectifiers in high frequency switched mode power supplies.

The BYQ40EW series is supplied in the conventional leaded SOT429 (TO247) package.

PINNING

PIN	DESCRIPTION
1	anode 1
2	cathode
3	anode 2
tab	cathode

SOT429 (TO247)



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MA	X.	UNIT
V _{RRM} V _{RWM} V _R	Peak repetitive reverse voltage Crest working reverse voltage Continuous reverse voltage	BYQ40EW	- - -	-150 150 150 150	-200 200 200 200	V V V
I _{O(AV)}	(both diodes conducting) Repetitive peak forward current	square wave $\delta = 0.5$; $T_{mb} \le 110 ^{\circ}\text{C}$ $t = 25 \mu\text{s}$; $\delta = 0.5$;	-	4		A A
I _{FSM}	per diode Non-repetitive peak forward current per diode	$T_{mb} \le 110 ^{\circ}C$ t = 10 ms t = 8.3 ms sinusoidal; with reapplied	- -	30 32		A A
I _{RRM}	Repetitive peak reverse current per diode	$ \begin{cases} V_{\text{RWM(max)}} \\ t_p = 2 \mu\text{s}; \end{cases} \delta = 0.001 $	-	0.	.2	A
I _{RSM}	Non-repetitive peak reverse current per diode	t _p = 100 μs	-	0.	.2	Α
T_{stg}	Storage temperature Operating junction temperature		-40 -		50 50	°C °C

ESD LIMITING VALUE

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _c	5	Human body model; C = 250 pF; R = 1.5 kΩ	ı	8	kV

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{\text{th j-mb}}$ $R_{\text{th j-a}}$	mounting base	per diode both diodes conducting in free air		- - 45	1.05 0.75 -	K/W K/W K/W

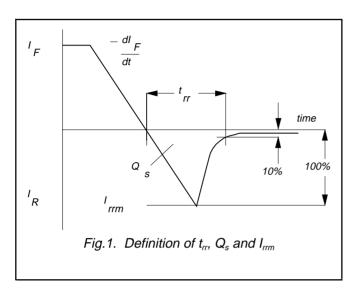
ELECTRICAL CHARACTERISTICS

characteristics are per diode at T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{F}	Forward voltage	$I_F = 20 \text{ A}; T_j = 150^{\circ}\text{C}$	1	8.0	0.85	V
		$I_{\rm F} = 20 {\rm A}$	-	0.97	1.05	V
		$I_{\rm F} = 40 \text{ A}$	-	1.06	1.20	V
l _R	Reverse current	$V_R = V_{RWM}$	-	6	100	μΑ
		$V_{R} = V_{RWM}$; $T_{i} = 100 ^{\circ}C$	-	0.7	1	mΑ
$Q_{\rm s}$	Reverse recovery charge	$V_R = V_{RWM}$; $T_j = 100 ^{\circ}C$ $I_F = 2 ^{\circ}A$; $V_R \ge 30 ^{\circ}V$; $-dI_F/dt = 20 ^{\circ}A/\mu s$	-	8	18	nC
t _{rr}	Reverse recovery time	$I_{\rm F} = 1 \text{ A}; V_{\rm R} \ge 30 \text{ V};$	-	23	30	ns
	_	$-dI_{F}/dt = 100 A/\mu s$				
V_{fr}	Forward recovery voltage	$I_F = 1 \text{ A}$; $dI_F/dt = 10 \text{ A/}\mu\text{s}$	-	0.7	-	V

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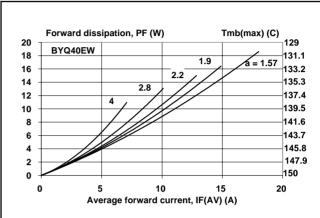
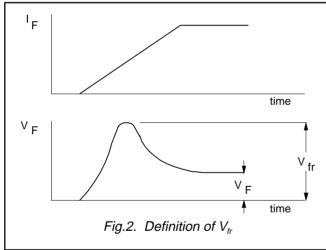
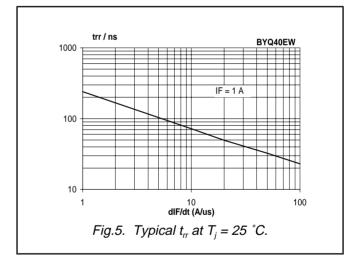


Fig.4. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; sinusoidal current waveform where a = f orm f actor $= I_{F(RMS)} / I_{F(AV)}$.





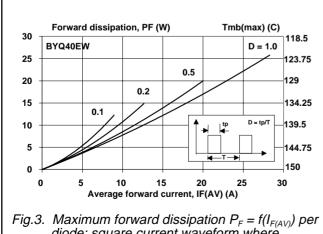
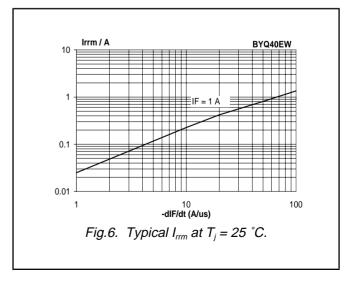
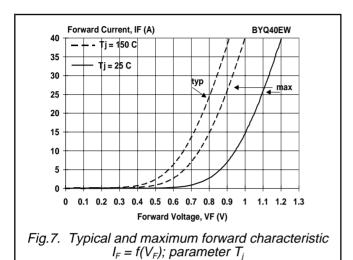


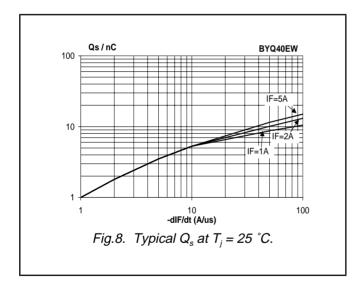
Fig.3. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; square current waveform where $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$.

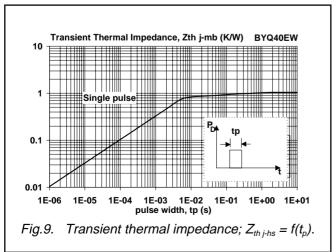


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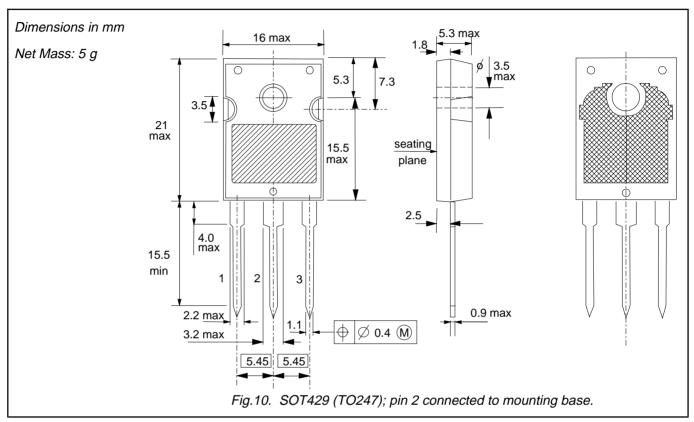




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MECHANICAL DATA



- Refer to mounting instructions for SOT429 envelope.
 Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

Rectifier diodes ultrafast, rugged

BYQ40EW series

DEFINITIONS

Data sheet status				
Objective specification	This data sheet contains target or goal specifications for product development.			
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.			
Product specification	This data sheet contains final product specifications.			
Limiting values				

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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